

LT5014s

16 × 16 Dot Matrix LEDs

■ Model No.

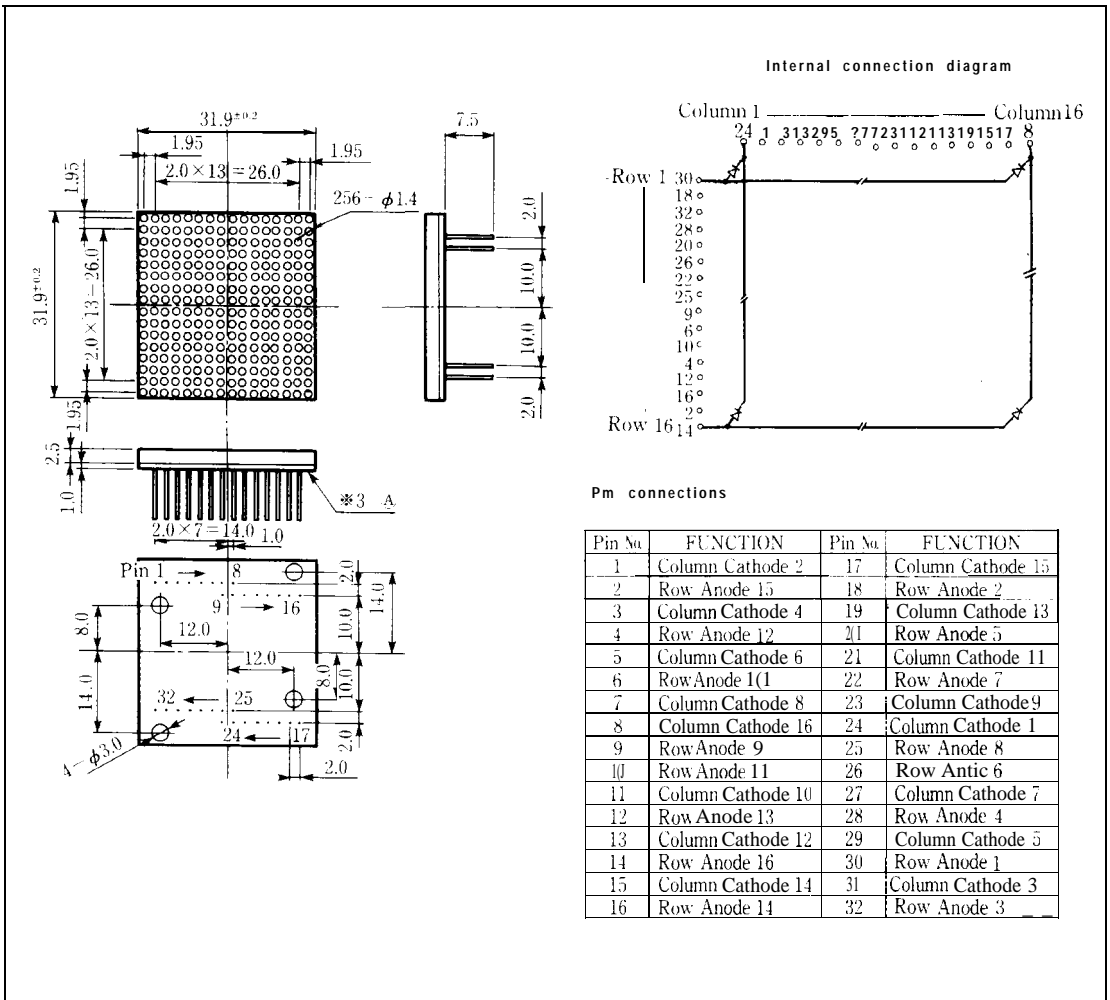
1. T5014S Sunset orange GaAsP/GaP

■ Features

1. Substrate type
2. 1.18" character height

■ Outline Dimensions

(Unit: mm)



LT5014s

■ Absolute Maximum Ratings

(Ta = 25°C)

Parameter	Symbol	LT5014S					Unit
*1 Power dissipation	P	1080					mW
Continuous forward current	Per dot I _F	15					mA
*2 Peak forward current	Per dot I _{FM}	80					mA
Derating factor	Per dot ' c	—					mA/°C
	Pulse	—	1.45				mA/°C
Reverse voltage	Per dot V _R	5					V
Operating temperature	T _{opr}	-20 to +60					°C
Storage temperature	T _{stg}	-20 to +80					°C
*3 Soldering temperature	T _{sol}	260 (within 5 seconds)					°C

※ 1 Per device

※ 2 Duty ratio = 1/16, Pulse width = 0.1ms, Lighting ratio = 30%

When the lighting ratio is over 30%, a heat sink must be installed.

※ 3 At the position of 2.6 mm from (A) level of outline dimensions

LT5014S(Sunset orange)

■ Electro-optical Characteristics ※4

(Ta = 25°C)

Parameter	Symbol	Model No.	Conditions	MIN.	TYP.	MAX.	Unit
Forward voltage	V _F	LT5014S	I _F = 10mA	-	1.9	-	V
		LT5014S	I _{FM} = 50mA	-	2.2	3.0	
“jLuminous intensity	I _v	LT5014S	I _F = 10mA	0.65	1.0	-	mcd
Peak emission wavelength	λ _p	LT5014S	I _{FM} = 50mA	-	610	-	nm
Spectrum radiation bandwidth	Δλ	LT5014S	I _{FM} = 50mA	-	35	-	nm
Reverse current	I _R	LT5014S	V _R = 4V	-	-	10	μA
Response frequency	f	LT5014S			4	-	MHz

※4 Per dot

※5 Tolerance: ±30%

■ Characteristics Diagrams

